

X-Band Solid State Power Amplifier Module 9.2-10 GHz, 1000 Watts MODEL BPMC928109-1000

Features:

- AB Linear Gallium Nitride (GaN) Technology
- High Output Power Dynamic Range
- Excellent Efficiency
- RF Input & Output Sample Detectors
- Pulse Width and Duty Factor Protection
- Thermal and Load VSWR Protection
- Optional Digital Interface for Control & Status Monitoring
- Optional Phase and Amplitude Control
- Suitable Building Block for Phased Array Systems



Performance Specifications

• Frequency Range: 9.2 to 10.0 GHz

Peak Output Power: 1000W
Power Gain: 60dB nominal
Power Gain Variation: ±2 dB (9.2-10Ghz)

• Pulse Width: 0.25 to 100 μs max

Duty Cycle: 10% max
Pulse Droop: <0.5dB
Pulse Rise & Fall Time: <60ns typical
Input VSWR: <1.5:1

Input VSWR: <1.5:1
 Output Load VSWR
 Load VSWR Protection: <2:1
 VSWR
 Output Fwd. & Ref. Sample: -50dBc

Harmonics:

2Fo: <-40dBc 3Fo: <-50dBc • RF Pulse: On-Off Isolation ≥ 110 dBc DC Voltage Input:DC Supply Current:RF to DC Efficiency:

Operating Temperature: Operating Humidity:

Operating Shock & Vibration:

Operating Shock & Vis
Operating Altitude:
Control Interface:

PA Enable/Disable:

PA Enable/Disable:RF Connectors:

RF Input and Sample Ports: RF Output:

• DC & Interface Connector:

Size:

Weight:

+28VDC ±1VDC

25.5 Amps nominal for 10% DF

14% nominal

-40°C to +65°C baseplate 0 to 95% non-condensing Per Mil-Std-810F

Per Mil-Std-810 10,000 Ft. RS-485 RS-422 (<1µS)

SMA

Type TNC (WG -90 optional) Combo-D-Subminiature

9.6" x 6.8" x 2.15"

5 lbs.

COMTECH PST proudly introduces a new Gallium Nitride (GaN) amplifier for applications in the X-Band radar market. The AB linear design operates over the 9.2-10.0 GHz frequency range intended for use in radar applications. The amplifier design features include options for control of phase and amplitude to allow for integration into high power systems utilizing conventional binary or phased array combining approaches for power levels of up to 10kW. Consistent with its planned technology development roadmap, Comtech is leading the field with the latest in GaN-based RF device performance and advanced amplifier development.